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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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EXAMINER

OWENS, DOUGLAS W

ART UNIT

PAPER NUMBER

2811

DATE MAILED: 05/28/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/903,160

Applicant(s)

BASCERI ET AL.

Examiner

Douglas W Owens

Art Unit

2811

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 14 January 2003.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-6, 8-13, 15-19, 21-29 and 38-44 is/are pending in the application.

4a) Of the above claim(s) _____ is/are withdrawn from consideration.

- 5) ☒ Claim(s) 9 - 13, 15 - 19, 21, 29, 38 - 41, 43 and 44 is/are allowed.

- 6) ☒ Claim(s) 1 - 3, 5, 6, 8, 22, 23, 25, 26, 28 and 42 is/are rejected.

- 7) ☒ Claim(s) 4, 24 and 27 is/are objected to.

- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892) 4) ☐ Interview Summary (PTO-413) Paper No(s). _____
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948) 5) ☐ Notice of Informal Patent Application (PTO-152)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 14. 6) ☐ Other: _____

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on January 6, 2003 has been entered.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

3. Claim 42 is rejected under 35 U.S.C. 102(e) as being anticipated by US patent No. 6,251,720 to Thakur et al.

Thakur et al. teaches a method for forming a capacitor comprising:
providing a non-oxide electrode (104; Fig. 1A, for example);
oxidizing an upper surface of the non-oxide electrode (Col. 8, lines 20 – 24);
depositing a high dielectric constant oxide dielectric material (102; Col. 9, lines 21 – 33) directly onto the oxidized surface (122) of the non-oxide electrode; and
depositing an upper layer electrode (106) on the high dielectric constant material.

Claim Rejections - 35 USC § 103

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

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(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

5. Claims 1 – 3, 5, 6, 8, 22, 23, 25, 26 and 28 rejected under 35 U.S.C. 103(a) as being unpatentable over US patent No. 6,251,720 to Thakur et al.

Regarding claims 1 and 2, Thakur et al. teaches a method for forming a capacitor comprising:

- providing a non-oxide electrode (104; Fig. 1A, for example);
- oxidizing an upper surface of the non-oxide electrode (Col. 8, lines 20 – 24);
- depositing a high dielectric constant oxide dielectric material (102; Col. 9, lines 21 – 33) directly onto the oxidized surface (122) of the non-oxide electrode; and
- depositing an upper layer electrode (106) on the high dielectric constant material.

Thakur et al. further teaches using an O₂ or N₂O gas to form the oxide. Thakur et al. does not teach using an O₃ plasma. It would have been obvious to one of ordinary skill in the art to select an O₃ plasma to form the oxide since it is a known gas that is well suited for the intended use.

Regarding claims 3 and 8, Thakur et al. teaches a method wherein the oxidation is carried out at a temperature in the range of 100 to 950 degrees Celsius (Col. 8, lines 45 – 52), which overlaps the claimed range of 250 to 700 and 250 to 500 degrees Celsius. In the case where the claimed ranges “overlap or lie inside ranges disclosed by the prior art” a *prima facie* case of obviousness exists. *In re Wertheim*, 541 F.2d 257, 191 USPQ 90 (CCPA 1976); *In re Woodruff*, 919 F.2d 1575, 16 USPQ2d 1934 (Fed. Cir. 1990).

Regarding claims 5 and 28, Thakur et al. teaches a method, wherein the high dielectric constant oxide is Ta_2O_5 (Col. 9, lines 29 – 33). It would have been obvious to one of ordinary skill to select Al_2O_3 or $\text{Ba}_x\text{Sr}_{(1-x)}\text{TiO}_3$, since they are known materials that are well suited for the intended use.

Regarding claim 6, Thakur et al. teaches that the upper surface is oxidized prior to the deposition of the high dielectric constant material. Thakur et al. does not explicitly teach that the oxidation is performed in an oxide deposition chamber. It would have been obvious to one of ordinary skill in the art to perform the oxidation in an oxidation deposition chamber since it is desirable to have a controlled environment so the oxide growth can be controlled.

Regarding claim 22, Thakur et al. teaches a method for forming a capacitor comprising:

- providing a non-oxide electrode;
- oxidizing an upper surface of the non-oxide electrode;
- depositing a high dielectric constant dielectric material directly onto the oxidized surface of the non-oxide electrode; and
- depositing an upper electrode.

Thakur et al. does not explicitly teach that the oxidation is performed in an oxide deposition chamber. It would have been obvious to one of ordinary skill in the art to perform the oxidation in an oxidation deposition chamber since it is desirable to have a controlled environment so the oxide growth can be controlled.

Thakur et al. does not teach depositing the high dielectric constant material in the same deposition chamber. It would have been obvious to one of ordinary skill in the art to leave the device in the controlled environment of the deposition chamber for depositing the high dielectric constant material, since it is desirable to reduce the number of process steps as well as minimizing the risks of contaminating the device during fabrication.

Regarding claims 23 and 26, Thakur et al. teaches a method for forming a capacitor comprising:

- providing a non-oxide electrode;
- oxidizing an upper surface of the non-oxide electrode in an atmosphere containing O₂ or N₂O;
- depositing a high dielectric constant dielectric material directly onto the oxidized surface of the non-oxide electrode; and
- depositing an upper electrode.

Thakur et al. further teaches a method wherein the oxidation is carried out at a temperature in the range of 100 to 950 degrees Celsius (Col. 8, lines 45 – 52), which overlaps the claimed ranges of 250 to 700 and 250 to 500degrees Celsius.

Regarding claim 25, Thakur et al. teaches a method for forming a capacitor comprising:

- providing a non-oxide electrode (104; Fig. 1A, for example);
- oxidizing an upper surface of the non-oxide electrode (Col. 8, lines 20 – 24) in an atmosphere containing O₂ or N₂O;

depositing a high dielectric constant oxide dielectric material (102; Col. 9, lines 21 – 33) directly onto the oxidized surface (122) of the non-oxide electrode; and depositing an upper layer electrode (106) on the high dielectric constant material.

Thakur et al. does not teach a gas plasma. It would have been obvious to one of ordinary skill in the art to use a plasma since it is a known material that is well suited for the intended use. Plasma is commonly used in the art to oxidize surfaces.

Allowable Subject Matter

6. Claims 4, 24 and 27 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

7. Claims 9 – 13, 15 – 19, 21, 29, 38 – 41, 43 and 44 are allowed.

The most closely related art, US patent No. 6,251,720 to Thakur et al. teaches away from oxidizing the lower electrode when a metallic layer is used for the bottom plate electrode (Col. 11, lines 33 – 37).

Response to Arguments

8. Applicant's arguments with respect to claims 1 – 3, 5, 6, 8, 22, 23, 25, 26, 28 and 42 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas W Owens whose telephone number is 703-308-6167. The examiner can normally be reached on Monday-Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on 703-308-2772. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

DWO
May 16, 2003

Steven Loh
Primary Examiner